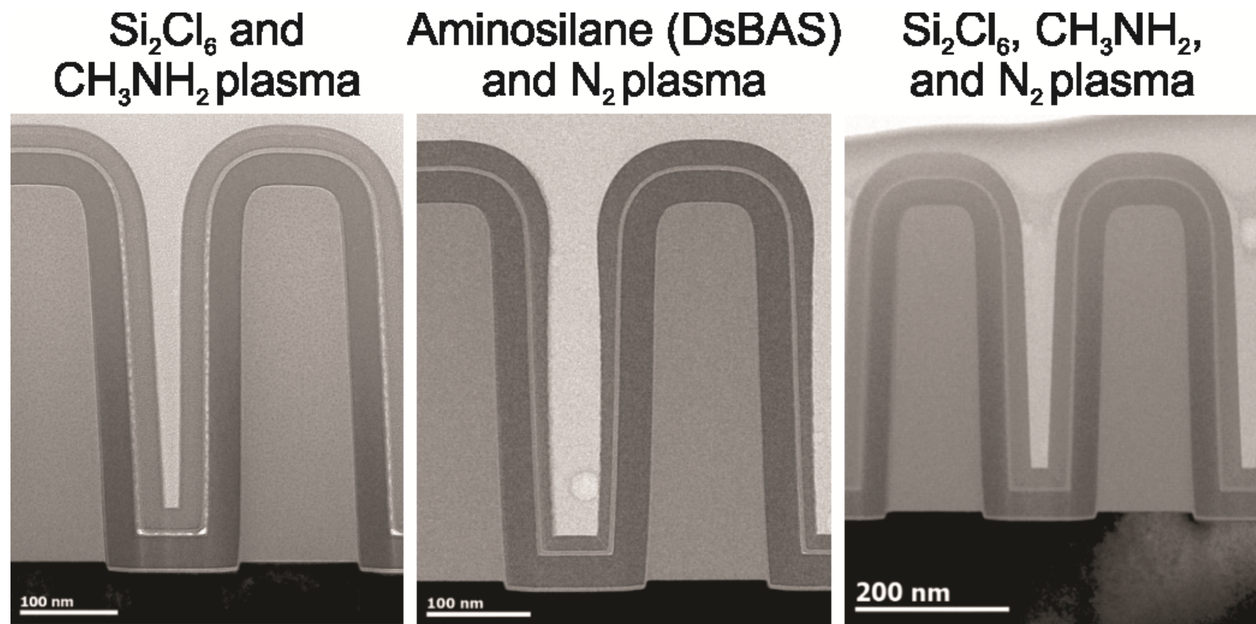

Figure 1: Cross-sectional transmission electron microscopy images of three ~25-nm-thick SiN_x films deposited using the Si_2Cl_6 and CH_3NH_2 plasma, di(*sec*-butylamino)silane (DsBAS) and N_2 plasma, and the Si_2Cl_6, CH_3NH_2, and N_2 plasma ALD processes. The substrate temperatures during deposition were 400, 375, and 400 °C, respectively.